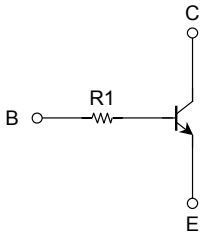
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) (Bias Resistor Built-in Transistor)

RN1910FE,RN1911FE

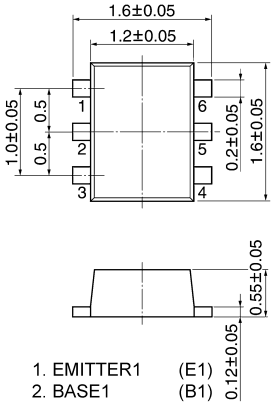
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Two devices are incorporated into an Extreme-Super-Mini (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN2910FE, RN2911FE

Equivalent Circuit and Bias Resistor Values



Unit: mm



ES6

JEDEC	—
JEITA	—
TOSHIBA	2-2N1G

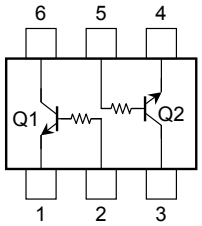
Weight: 0.003 g (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C (Note)	100	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Note: Total rating

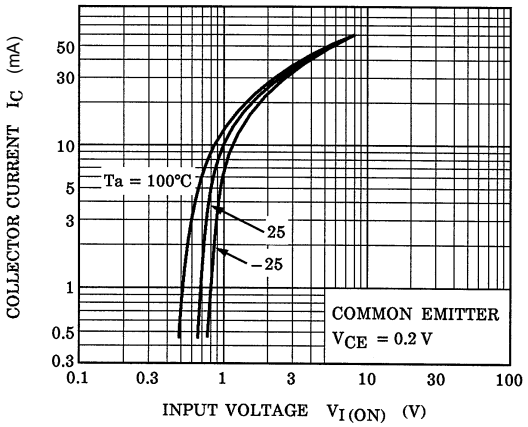
Equivalent Circuit (top view)



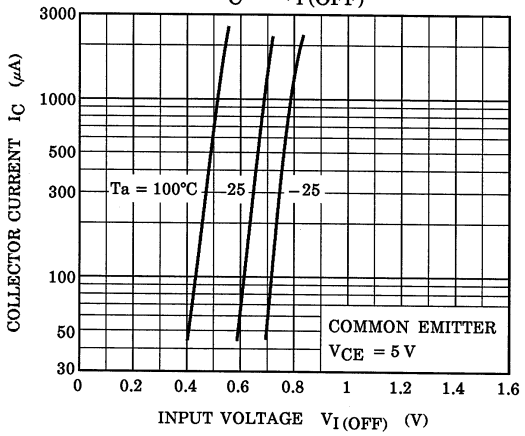
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = 50 V, I_E = 0	—	—	100	nA
Emitter cut-off current		I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	100	nA
DC current gain		h_{FE}	V_{CE} = 5 V, I_C = 1 mA	120	—	700	
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 5 mA, I_B = 0.25 mA	—	0.1	0.3	V
Transition frequency		f_T	V_{CE} = 10 V, I_C = 5 mA	—	250	—	MHz
Collector output capacitance		C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	RN1910FE	R1	—	3.29	4.7	6.11	kΩ
	RN1911FE			7	10	13	

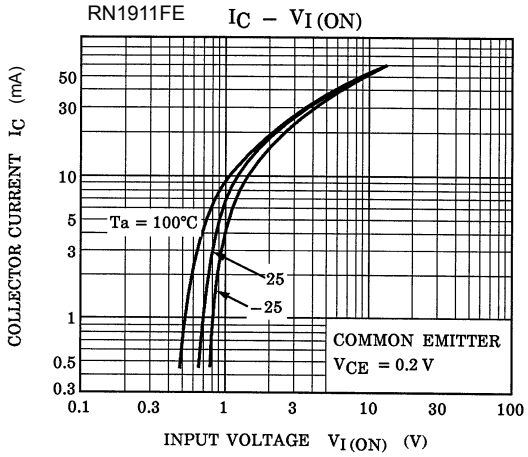
RN1910FE $I_C - V_{I(ON)}$



RN1910FE $I_C - V_{I(OFF)}$



RN1911FE $I_C - V_{I(ON)}$



RN1911FE $I_C - V_{I(OFF)}$